ON Semiconductor

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4-Pin DIP Phototransistor Optocouplers

FOD785 Series

Description

The FOD785 series is a general-purpose family of phototransistor optocoupler. It is offered in various CTR bins to meet the needs of most applications. It consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a compact 4-pin dual in-line package.

Features

• Wide Selection in Current Transfer Ratio (CTR):

FOD785: 50 - 600%FOD785A: 80 – 160% FOD785B: 130 – 260% FOD785C: 200 – 400% FOD785D: 300 – 600%

- Safety and Regulatory Approvals:
 - UL1577, 5,000 VACRMS for 1 Minute
 - ◆ DIN EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

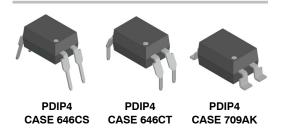
Typical Applications

- Digital Logic Inputs
- Microprocessor Inputs
- Power Supply Monitor
- Twisted Pair Line Receiver
- Telephone Line Receiver

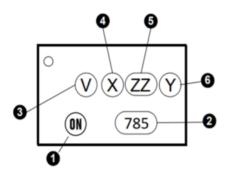


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MARKING DIAGRAM



1. ON = Company Logo

2. 785 = Device Number

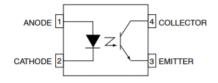
= DIN EN/IEC60747-5-5 Option 3. V

4. X = One-Digit Year Code

5. ZZ = Two-Digit Work Week

= Assembly Package Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

Safety and Insulation Ratings

As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Table 1. SAFETY AND INSULATION RATINGS

Parameter		Characteristics
	< 300 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 600 V _{RMS}	I–III
Climatic Classification	55/110/21	
Pollution Degree (DIN VDE 0110/1.89)	2	
Comparative Tracking Index		175

Table 2.

Symbol	Symbol Parameter		Unit
V _{PR}	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V _{peak}
	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1594	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	850	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6000	V _{peak}
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option W, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T _S	T _S Case Temperature (Note 1) 175		°C
I _{S,INPUT}	Input Current (Note 1)	130	mA
P _{S,OUTPUT}	Output Power (Note 1)	265	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	> 10 ¹¹	Ω

^{1.} Safety limit values – maximum values allowed in the event of a failure.

Table 3. ABSOLUTE MAXIMUM RATINGS

Symbol	Symbol Parameter Value		Unit
TOTAL PACKAGE		·	
T _{STG}	Storage Temperature	-55 to +125	°C
T _{OPR}	Operating Temperature	-55 to +110	°C
T _J	Junction Temperature	-55 to +125	°C
T _{SOL}	Lead Solder Temperature 260 for 10 secon		°C
P _{TOT}	P _{TOT} Total Device Power Dissipation 200		mW
EMITTER			
I _F	Continuous Forward Current	50	mA
V _R	Reverse Voltage	6	V
P _D	Power Dissipation	100	mW
	Derate Above 100°C	2.9	mW/°C

Table 3. ABSOLUTE MAXIMUM RATINGS (continued)

Symbol	Parameter	Value	Unit			
DETECTOR	DETECTOR					
V _{CEO}	Collector-Emitter Voltage	80	V			
V _{ECO}	Emitter-Collector Voltage	6	V			
I _C	Continuous Collector Current 50		mA			
P _C	P _C Collector Power Dissipation		mW			
	Derate Above 100°C	5.8	mW/°C			

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Electrical Characteristics

Table 4. ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
EMITTER						
V _F	Forward Voltage	I _F = 20 mA		1.2	1.4	V
I _R	Reverse Current	V _R = 4.0 V			10	μΑ
Ct	Terminal Capacitance	V = 0, f = 1 kHz		30		pF
DETECTO	OR .					
I _{CEO}	Collector Dark Current	V _{CE} = 20 V, I _F = 0			100	nA
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 0.1 mA, I _F = 0	80			V
BV _{ECO}	Emitter-Collector Breakdown Voltage	I _E = 0.01 mA, I _F = 0	6			V
DC TRAN	ISFER CHARACTERISTICS					
CTR	Current Transfer Ratio - FOD785	I _F = 5 mA, V _{CE} = 5 V	50		600	%
(Note 2)	- FOD785A		80		160	
	- FOD785B		130		260	
	- FOD785C		200		400	
	- FOD785D		300		600	
V _{CE(SAT)}	Saturation Voltage	I _F = 20 mA, I _C = 1 mA			0.2	V
AC TRAN	ISFER CHARACTERISTICS					
t _r	Rise Time	I_C = 2 mA, V_{CE} = 2 V, R_L = 100 Ω			18	μs
t _f	Fall Time	(Note 3)			18	μs
F _{CO}	Cut-Off Frequency			80		kHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Table 5. ISOLATION CHARACTERISTICS (T_A = 25°C unless otherwise specified)

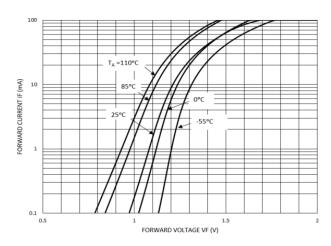
Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _{ISO}	Input-Output Isolation Voltage (Note 4)	f = 60 Hz, t = 1 minutes, $I_{I-O} \leq 2~\mu A$	5000			VAC _{RMS}
R _{ISO}	Isolation Resistance	V _{I-O} = 500 V _{DC}		1 x 10 ¹¹		Ω
C _{ISO}	Isolation Capacitance	$V_{I-O} = 0$, $f = 1$ MHz		0.6	1.0	pf

^{4.} For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.

^{2.} Current Transfer Ratio (CTR) = I_C / I_F x 100%.

^{3.} Refer to test circuit setup.

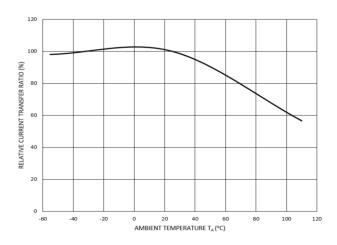
TYPICAL CHARACTERISTICS



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Figure 1. Forward Current vs. Forward Voltage

Figure 2. Current Transfer Ratio vs. Forward Current



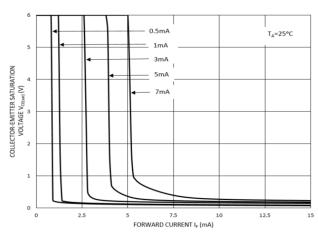
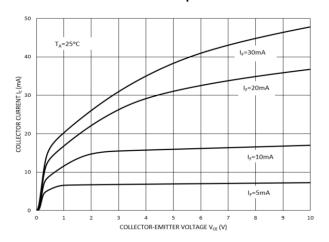


Figure 3. Relative Current Transfer Ratio vs.
Ambient Temperature

Figure 4. Collector-Emitter Saturation Voltage vs. Forward Current



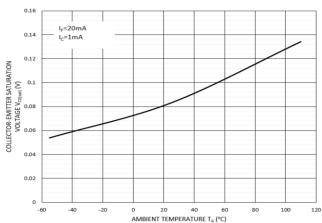
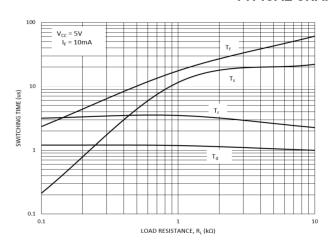


Figure 5. Collector Current vs. Collector-Emitter Voltage

Figure 6. Collector-Emitter Saturation Voltage vs. Ambient Temperature

TYPICAL CHARACTERISTICS



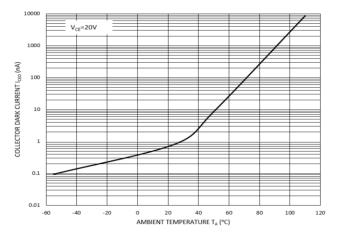
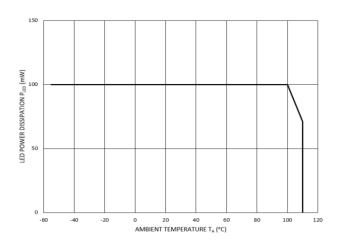


Figure 7. Switching Time vs. Load Resistance

Figure 8. Switching Time vs. Load Resistance



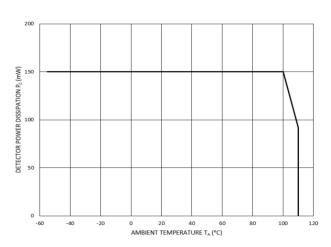


Figure 9. Max Allowable Power Dissipation (LED) vs. Ambient Temperature

Figure 10. Max Allowable Power Dissipation (Detector) vs. Ambient Temperature

Test Circuit

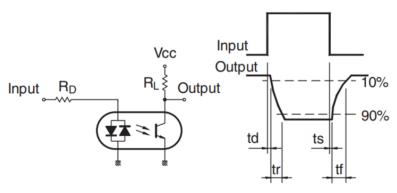


Figure 11. Test Circuit

Reflow Profile

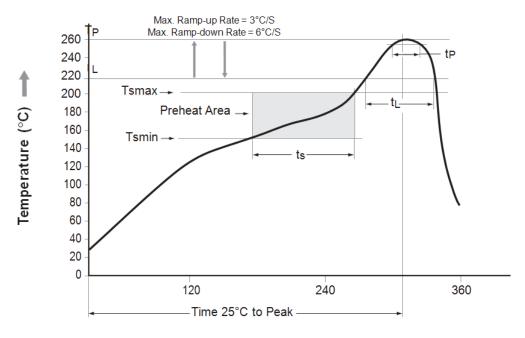


Figure 12. Reflow Profile

Table 6.

Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60-150 seconds
Peak Body Package Temperature	260°C +0°C / –5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C / second max.
Time 25°C to Peak Temperature	8 minutes max.

Table 7. ORDERING INFORMATION

Part Number	Package	Packing Method [†]
FOD785	DIP 4-Pin	Tube (100 units per tube)
FOD785S	SMT 4-Pin (Lead Bend)	Tube (100 units per tube)
FOD785SD	SMT 4-Pin (Lead Bend)	Tape and Reel (1,500 units per reel)
FOD785300	DIP 4-Pin, DIN EN/IEC60747-5-5 option	Tube (100 units per tube)
FOD7853S	SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option	Tube (100 units per tube)
FOD7853SD	SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option	Tape and Reel (1,500 units per reel)
FOD785300W	DIP 4-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 option	Tube (100 units per tube)

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NOTE: The product orderable part number system listed in this table also applies to the FOD785A, FOD785B, FOD785C, and FOD785D products.

PACKAGE DIMENSIONS

PDIP4 6.50mm (STANDARD LEAD FORM)

CASE 646CS ISSUE O

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

MAX.

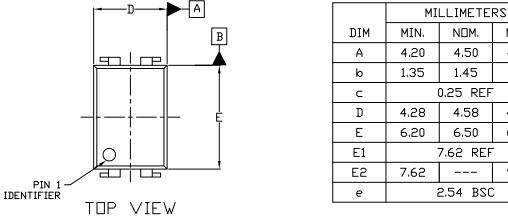
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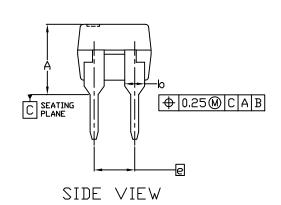
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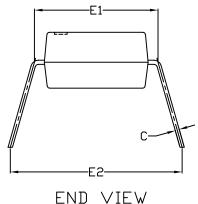
4.88

6.80

9.50







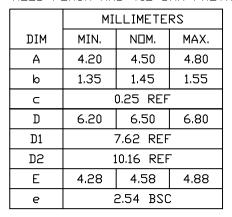
PACKAGE DIMENSIONS

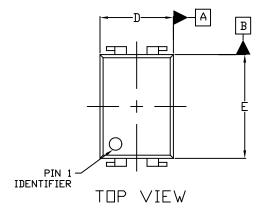
PDIP4 6.50mm (M LEAD FORM)

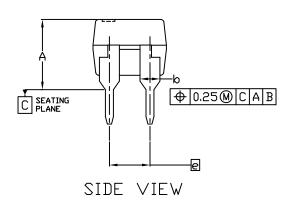
CASE 646CT ISSUE O

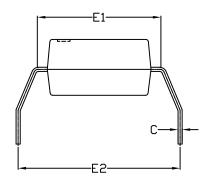
NOTES:

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- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.









END VIEW

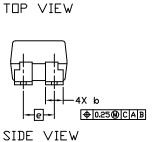
PACKAGE DIMENSIONS

PDIP4 6.50mm (GULL WING)

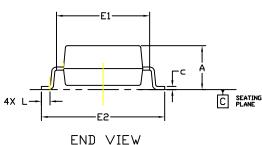
CASE 709AK **ISSUE O**

NOTES:

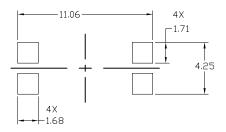
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- FOOT LENGTH, DIMENSION L, IS MEASURED AS THE FLAT PORTION OF THE LEAD FOOT.



PIN 1 IDENTIFIER



	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	3.30	3.60	3.90	
b	1.35	1.45	1.55	
U	0.25 REF			
D	4.28	4.58	4.88	
Ε	6.20	6.50	6.80	
E1	7.62 REF			
E2			10.30	
e	2.54 BSC			
L	0.60			



RECOMMENDED MOUNTING FOOTPRINT*

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

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